



钜地半导体
Tudi Semiconductor

Product Specification

TUDI-AO4803A

30V Dual P-Channel MOSFET

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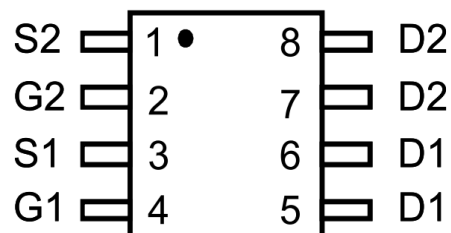
**semiconductor device
manufacturer**

- Design
- research and development
- production
- and sales



General Description

The AO4803A uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications.



Absolute Maximum Ratings $T_A=25^{\circ}\text{C}$ unless otherwise noted				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	-5	A
	$T_A=70^{\circ}\text{C}$		-4	
Pulsed Drain Current ^C		I_{DM}	-30	
Avalanche Current ^C		I_{AS}, I_{AR}	17	A
Avalanche energy $L=0.1\text{mH}$ ^C		E_{AS}, E_{AR}	14	mJ
Power Dissipation ^B	$T_A=25^{\circ}\text{C}$	P_D	2	W
	$T_A=70^{\circ}\text{C}$		1.3	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	$R_{\theta JA}$	48	62.5	$^{\circ}\text{C/W}$
Maximum Junction-to-Ambient ^{A D}	Steady-State		74	110	$^{\circ}\text{C/W}$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	35	40	$^{\circ}\text{C/W}$



Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-1.5	-2	-2.5	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-5A T _J =125°C		32 48	46 68	mΩ
		V _{GS} =-4.5V, I _D =-4A		51	74	
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-5A		13		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Maximum Body-Diode Continuous Current				-2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		520		pF
C _{oss}	Output Capacitance			100		pF
C _{rss}	Reverse Transfer Capacitance			65		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	3.5	7.5	11.5	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-5A		9.2	11	nC
Q _g (4.5V)	Total Gate Charge			4.6	6	nC
Q _{gs}	Gate Source Charge			1.6		nC
Q _{gd}	Gate Drain Charge			2.2		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-15V, R _L =3Ω, R _{GEN} =3Ω		7.5		ns
t _r	Turn-On Rise Time			5.5		ns
t _{D(off)}	Turn-Off DelayTime			19		ns
t _f	Turn-Off Fall Time			7		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-5A, di/dt=100A/μs		11		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-5A, di/dt=100A/μs		5.3		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

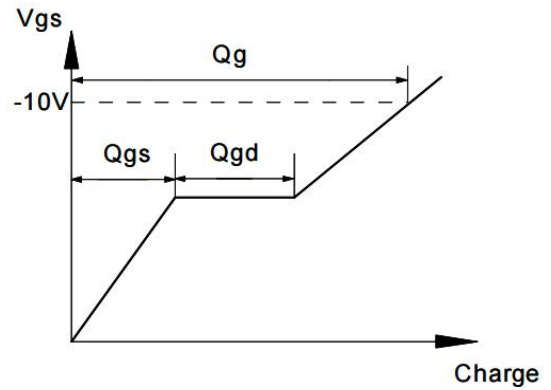
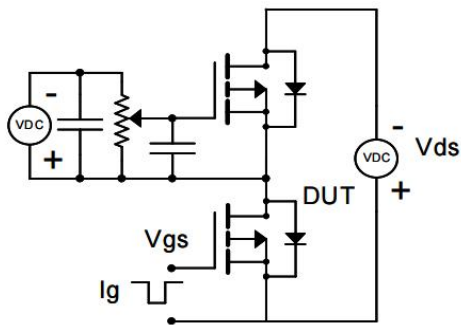
D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

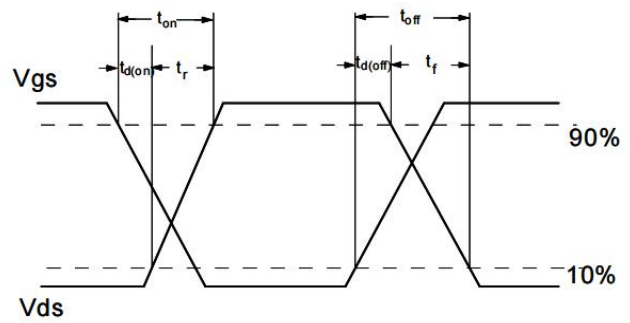
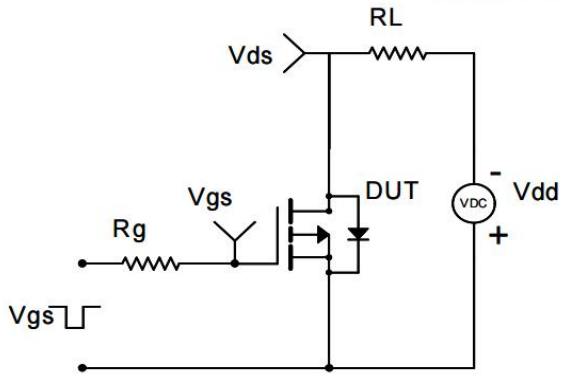
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.



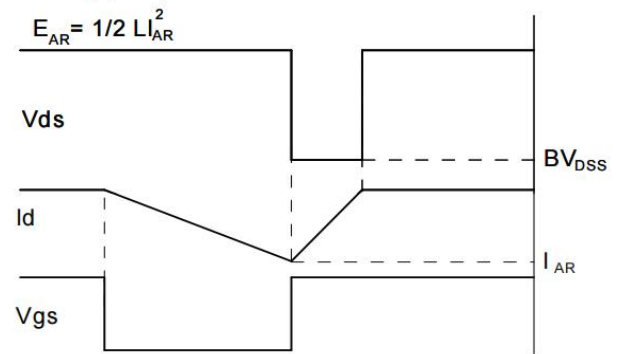
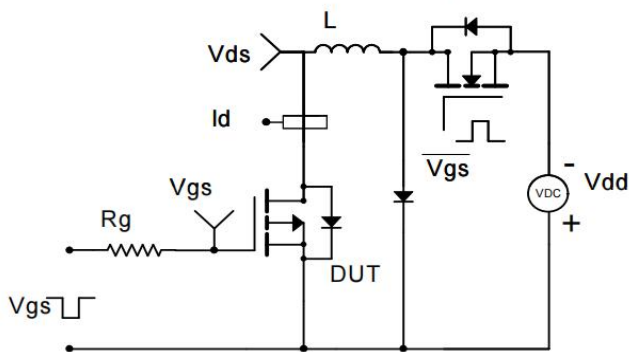
Gate Charge Test Circuit & Waveform



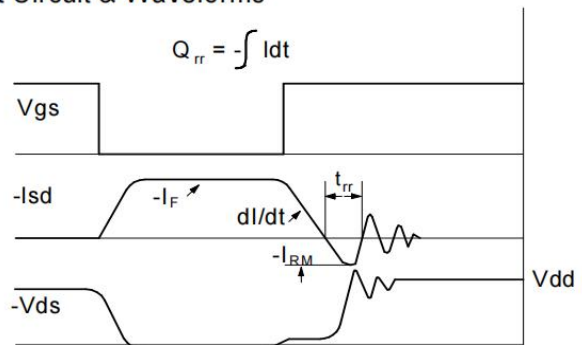
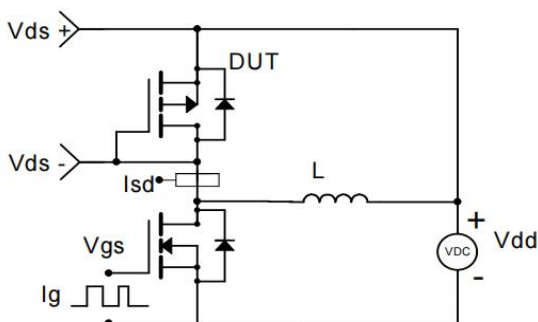
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



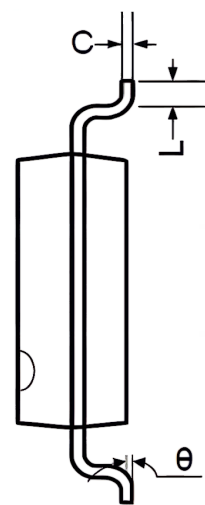
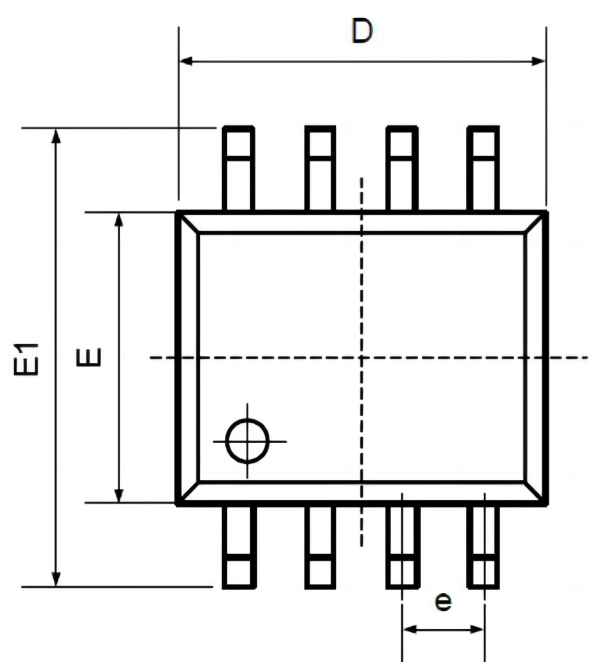


Order information

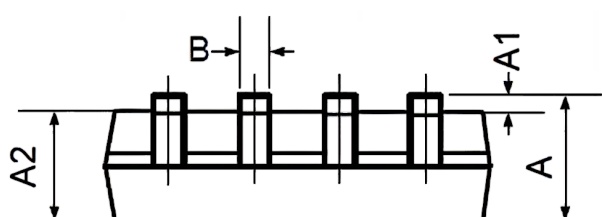
Order Number	Package	Package Quantity	Marking On The park
AO4803A-TUDI	SOP8	Tape,Reel,2500	AO4803A



Package SOP8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
B	0.330	0.510	0.013	0.020
C	0.190	0.250	0.007	0.010
D	4.780	5.000	0.188	0.197
E	3.800	4.000	0.150	0.157
E1	5.800	6.300	0.228	0.248
e	1.270TYP		0.050TYP	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°





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